

HSK110

Silicon Epitaxial Planar Diode for UHF/VHF tuner Band Switch

HITACHI

 Rev. 1
 Jun. 1994

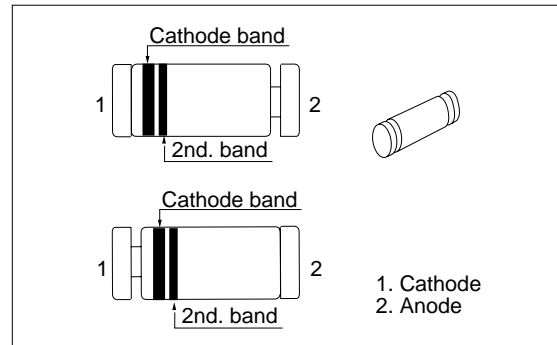
Features

- Low forward resistance. ($r_f = 0.9\Omega$ max)
- LLD package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Cathode band	2nd.band	Package code
HSK110	White	Blue	LLD

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	35	V
Forward current	I_F	100	mA
Operation temperature	T_{opr}	-20 to + 60	°C
Storage temperature	T_{stg}	-55 to +125	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	0.65	—	1.05	V	$I_F = 1$ mA
Reverse voltage	V_R	35	—	—	V	$I_R = 1$ μ A
Reverse current	I_R	—	—	0.1	μ A	$V_R = 25$ V
Capacitance	C	—	—	1.2	pF	$V_R = 6$ V , $f = 1$ MHz
Forward resistance	r_f	—	—	0.9	Ω	$I_F = 2$ mA , $f = 100$ MHz

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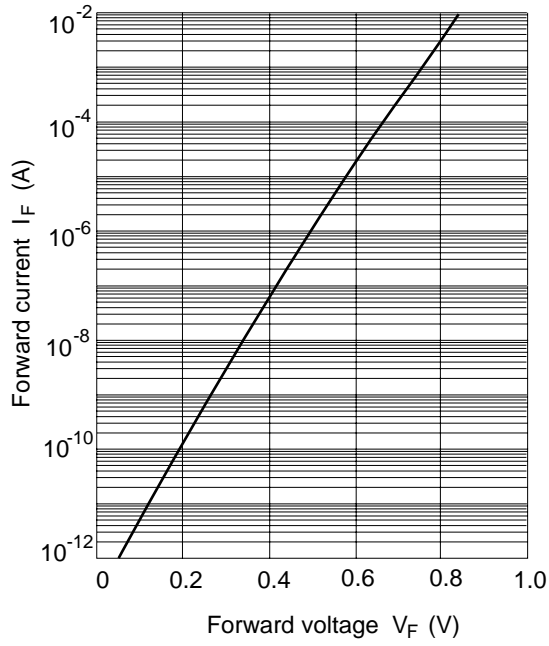


Fig.1 Forward current Vs. Forward voltage

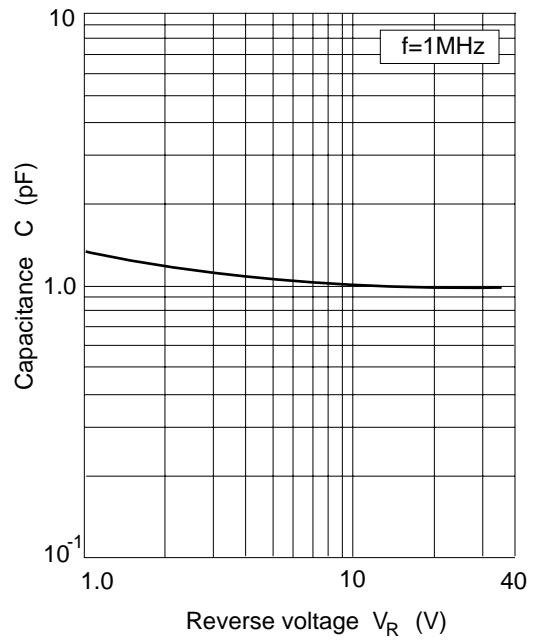


Fig.2 Capacitance Vs. Reverse voltage

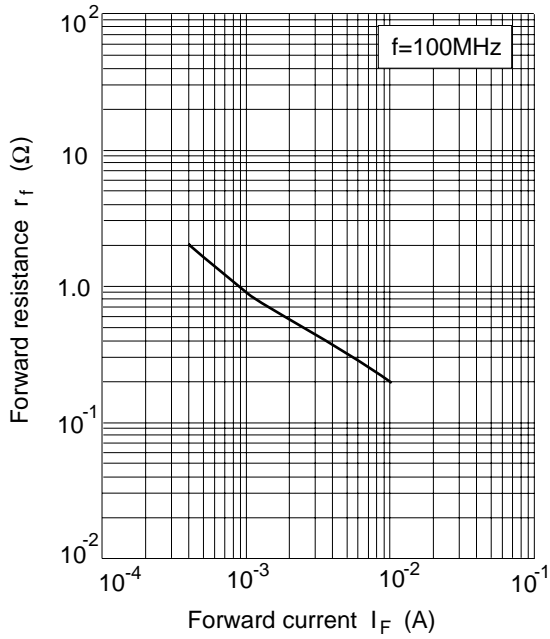
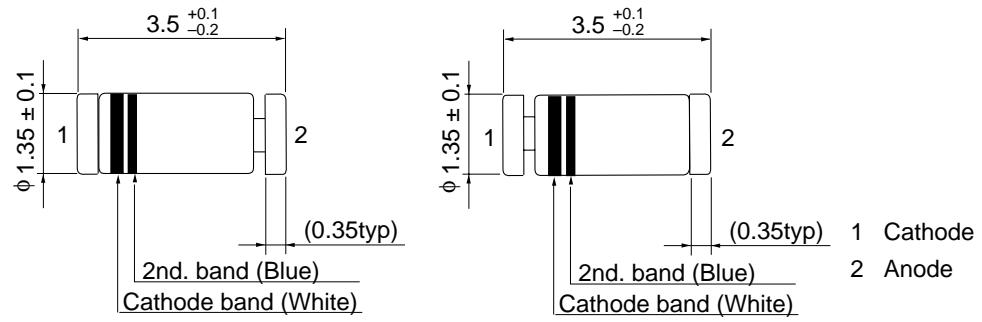


Fig.3 Forward resistance Vs. Forward current

Package Dimensions

Unit: mm



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HITACHI Code	LLD
JEDEC Code	—
EIAJ Code	—
Weight (g)	0.027